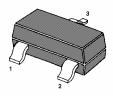
MMBTSC2223

NPN Silicon Epitaxial Planar Transistor

High frequency amplifier

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.



1.BASE 2.EMITTER 3.COLLECTOR SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	20	V
Emitter-Base Voltage	V _{EBO}	4	V
Collector Current	Ι _C	20	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	℃
Storage Temperature Range	Ts	-55 +150	°C

Characteristics at Tamb=25 °C

Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at V_{CE} = 6 V, I_C = 1 mA Current Gain Group R O Y	h _{FE} h _{FE} h _{FE}	40 60 90	- - -	80 120 180	- - -
Collector Emitter Saturation Voltage at I_c = 10 mA, I_B = 1 mA	V _{CE(sat)}	-	-	0.3	V
Collector Cutoff Current at V_{CB} = 30 V	I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current at V _{EB} = 4 V	I _{EBO}	-	-	0.1	μA
Collector Base Breakdown Voltage at $I_c = 10 \ \mu A$	V _{(BR)CBO}	30			V
Collector Emitter Breakdown Voltage at $I_c = 1 \text{ mA}$	V _{(BR)CEO}	20	-	-	V
Emitter Base Breakdown Voltage at I _E = 10 μA	V _{(BR)EBO}	4	-	-	V
Gain Bandwidth Product at V_{CE} = 6 V, -I _E =1 mA	f _T	400	600	-	MHz
Output Capacitance at V_{CB} = 6 V, I_E = 0, f = 1 MHz	C _{OB}	-	1	-	pF
Collector to Base Time Constant at V_{CE} = 6 V, -I _E = 1 mA, f = 31.9 MHz	C _c -rb'b	-	12	-	ps
Noise Figure at V_{CE} = 6 V, -I _E = 1 mA, f = 100 MHz, R _G = 50 Ω	NF	-	3	-	dB

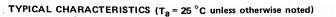


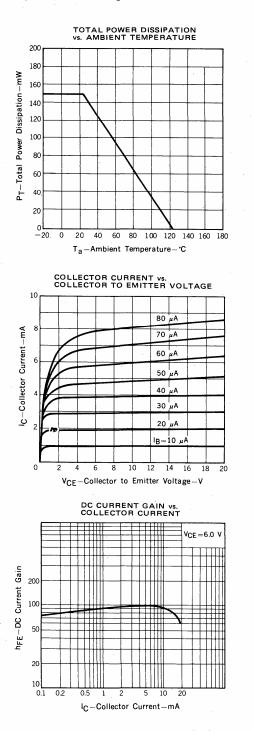
SEMTECH ELECTRONICS LTD.

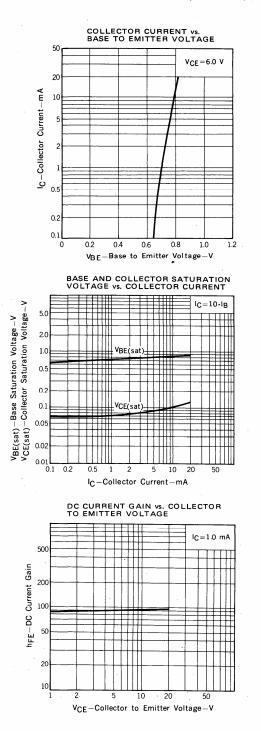
(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 14/12/2005





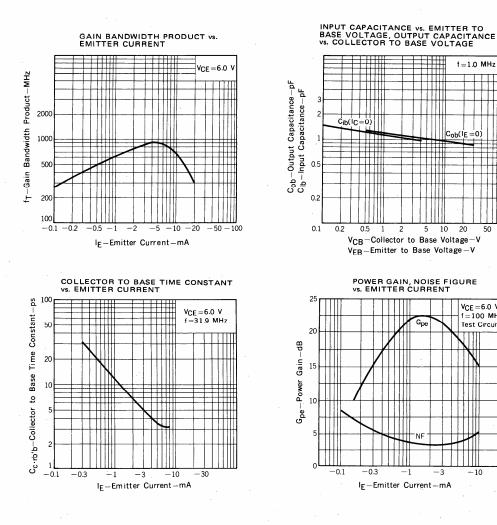








Dated : 14/12/2005









f = 1.0 MHz

=0

20

50

V_{CE} = 6.0 V f = 100 MHz

Test Circuit

-10

Bb

NF-Noise Figure-

2 5 10

Gp

Dated : 14/12/2005